

AMENDMENTS TO THE ABSTRACT

Please replace the ABSTRACT with the following:

Methods for grinding low-K interlayer dielectric (ILD) wafers are described herein. In various embodiments, the method may include cutting and severing a semiconductor wafer into a plurality of portions, the cutting and severing being performed in a manner that allows the portions to remain disposed with each other as if the semiconductor wafer had not been cut, applying a tape to a front side of the as if uncut semiconductor wafer, and grinding a backside of the taped as if uncut semiconductor wafer. In various other embodiments, the method may include attaching an adhesive to a backside of the semiconductor wafer prior to cutting the semiconductor wafer along the streets of the semiconductor wafer with the scribed lines to cut and sever the semiconductor wafer into a plurality of portions, with the portions remaining proximally disposed to each other and held in place by the adhesive as if the semiconductor device had not been cut.